256K (32K x 8) Paged CMOS E^2PROM

Features

- **Fast Read Access Time - 150ns**
- **Automatic Page Write Operation**
  - **Internal Address and Data Latches for 64 Bytes**
  - **Internal Control Timer**
- **Fast Write Cycle Times**
  - **Page Write Cycle Time: 3.0ms or 10ms maximum**
  - **1 to 64 Byte Page Write Operation**
- **Low Power Dissipation**
  - **80mA Active Current**
  - **200µA CMOS Standby Current**
- **Hardware and Software Data Protection**
- **DATA Polling for End of Write Detection**
- **High Reliability CMOS Technology**
  - **Endurance: 10^4 or 10^5 Cycles**
  - **Data Retention: 10 years**
- **Single 5V ± 10% Supply**
- **CMOS and TTL Compatible Inputs and Outputs**
- **JEDEC Approved Byte-Wide Pinout**
- **Full Military, Commercial, and Industrial Temperature Ranges**

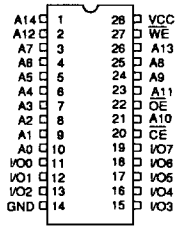
Description

The AT28C256 is a high-performance Electrically Erasable and Programmable Read Only Memory. Its 256k of memory is organized as 32,768 words by 8 bits. Manufactured with Atmel's advanced non-volatile CMOS technology, the device offers access times to 150ns with power dissipation of just 440mW. When the device is deselected, the CMOS standby current is less than 200µA.

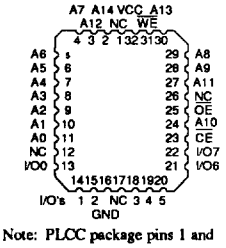
The AT28C256 is accessed like a Static RAM for the read or write cycle without the need for external components. The device contains a 64-byte page register to allow writing of up to 64 bytes simultaneously. During a write cycle, the addresses and 1 to 64 bytes of data are internally latched, freeing the address and data bus for other operations. Following the initiation of a write cycle, the device will automatically write the latched data using an internal control timer. The end of a write cycle can be detected by DATA polling of I/O7. Once the end of a write cycle has been detected a new access for a read or write can begin.

Atmel's 28C256 has additional features to ensure high quality and manufacturability. The device utilizes internal error correction for extended endurance and improved data retention characteristics. An optional software data protection mechanism is available to guard against inadvertent writes. The device also includes an extra 64 bytes of E^2PROM for device identification or tracking.

Pin Configurations

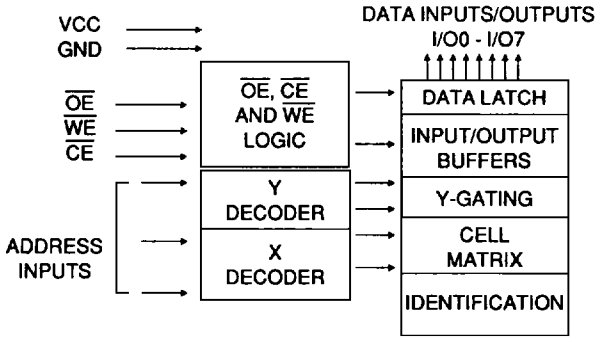


Pin Name	Function
A0 - A14	Addresses
$\overline{CE}$	Chip Enable
$\overline{OE}$	Output Enable
$\overline{WE}$	Write Enable
I/O0 - I/O7	Data Inputs/Outputs
NC	No Connect



Note: PLCC package pins 1 and 17 are DON'T CONNECT.

Block Diagram



Device Operation

READ: The AT28C256 is accessed like a Static RAM. When $\overline{CE}$ and $\overline{OE}$ are low and $\overline{WE}$ is high, the data stored at the memory location determined by the address pins is asserted on the outputs. The outputs are put in the high impedance state whenever $\overline{CE}$ or $\overline{OE}$ is high. This dual line control gives designers flexibility in preventing bus contention.

WRITE: A low pulse on the $\overline{WE}$ or $\overline{CE}$ input with $\overline{CE}$ or $\overline{WE}$ low (respectively) and $\overline{OE}$ high initiates a write cycle. The address is latched on the falling edge of $\overline{CE}$ or $\overline{WE}$, whichever occurs last. The data is latched by the first rising edge of $\overline{CE}$ or $\overline{WE}$. Once a byte write has been started it will automatically time itself to completion.

PAGE WRITE MODE: The page write operation of the AT28C256 allows one to 64 bytes of data to be loaded into the device and then simultaneously written during the internal programming period. After the first data byte has been loaded into the device successive bytes may be loaded in the same manner. Each new byte to be written must have its high to low transition on $\overline{WE}$ (or $\overline{CE}$) within 150µs of the low to high transition of $\overline{WE}$ (or $\overline{CE}$) of the preceding byte. If a high to low transition is not detected within 150µs of the last low to high transition, the load period will end and the internal programming period will start. A6 to A14 specify the page address. The page address must be valid during each high to low transition of $\overline{WE}$ (or $\overline{CE}$). A0 to A5 are used to specify which bytes within the page are to be written. The bytes may be loaded in any order and may be changed within the same load period. Only bytes which are specified for writing will be written; unnecessary cycling of other bytes within the page does not occur.

$\overline{DATA}$ POLLING: The AT28C256 features $\overline{DATA}$ Polling to indicate the end of a write cycle. During a byte or page write cycle an attempted read of the last byte written will result in the complement of the written data on I/O7. Once the write cycle has been completed, true data is valid on all outputs, and the next cycle may begin. DATA Polling may begin at any time during the write cycle.

TOGGLE BIT: In addition to $\overline{DATA}$ Polling the AT28C256 provides another method for determining the end of a write cycle. During a write operation, successive attempts to read data from the device will result in I/O6 toggling between one and zero. Once the write has completed, I/O6 will stop toggling and valid data will be read. Examining the toggle bit may begin at any time during the write cycle.

HARDWARE DATA PROTECTION: Hardware features protect against inadvertent writes to the AT28C256 in the following ways: (a) Vcc sense— if Vcc is below 3.8V (typical) the write function is inhibited. (b) Vcc power on delay— once Vcc has reached 3.8V the device will automatically time out 5ms (typical) before allowing a write. (c) Write inhibit— holding any one of $\overline{OE}$ low, $\overline{CE}$ high or $\overline{WE}$ high inhibits write cycles. (d) Noise filter— pulses of less than 15ns (typical) on the $\overline{WE}$ or $\overline{CE}$ inputs will not initiate a write cycle.

SOFTWARE DATA PROTECTION: A software controlled data protection feature is available on the AT28C256. Once the software protection is enabled a software algorithm must be issued to the device before a write may be performed. The software protection feature may be enabled or disabled by the user; when shipped from Atmel, the software data protection feature is disabled. To enable the software data protection, a series of three write commands to specific addresses with specific data must be performed. After the software data protection is enabled the same three write commands must begin each write cycle in order for the writes to occur. All software write commands must obey the page write timing specifications. Once set, the software data protection feature remains active unless its disable command is issued. Power transitions will not reset the software data protection feature, but the software feature will guard against inadvertent writes during power transitions.

DEVICE IDENTIFICATION: An extra 64 bytes of E^2PROM memory are available to the user for device identification. By raising A9 to 12 ± 0.5V and using address locations 7FC0H to 7FFFH the additional bytes may be written to or read from in the same manner as the regular memory array.

Absolute Maximum Ratings*

Temperature Under Bias	-55°C to +125°C
Storage Temperature	-65°C to +150°C
All Input Voltages (including N.C. Pins) with Respect to Ground	-0.6V to +6.25V
All Output Voltages with Respect to Ground	-0.6V to V_{CC} +0.6V
Voltage on $\overline{OE}$ and A9 with Respect to Ground	-0.6V to +13.5V

*NOTICE: Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

D.C. and A.C. Operating Range

		AT28C256-15	AT28C256-20	AT28C256-25	AT28C256-35
Operating Temperature (Case)	Com.	0°C - 70°C	0°C - 70°C	0°C - 70°C	
	Ind.	-40°C - 85°C	-40°C - 85°C	-40°C - 85°C	
	Mil.	-55°C - 125°C	-55°C - 125°C	-55°C - 125°C	-55°C - 125°C
V_{CC} Power Supply		5V±10%	5V±10%	5V±10%	5V±10%

Operating Modes

Mode	$\overline{CE}$	$\overline{OE}$	$\overline{WE}$	I/O
Read	V_{IL}	V_{IL}	V_{IH}	D_{OUT}
Write[2]	V_{IL}	V_{IH}	V_{IL}	D_{IN}
Standby/Write Inhibit	V_{IH}	X[1]	X	High Z
Write Inhibit	X	X	V_{IH}	
Write Inhibit	X	V_{IL}	X	
Output Disable	X	V_{IH}	X	High Z
Chip Erase	V_{IL}	V_H [3]	V_{IL}	High Z

Notes: 1. X can be V_{IL} or V_{IH}.
2. Refer to A.C. Programming Waveforms.
3. $V_H = 12.0V \pm 0.5V$.

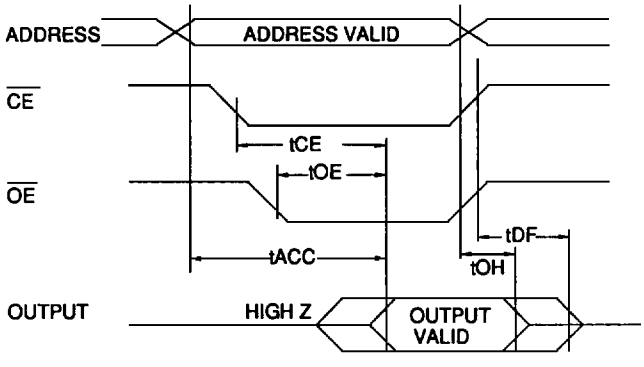
D.C. Characteristics

Symbol	Parameter	Condition		Min	Max	Units
I_{LI}	Input Load Current	V_{IN}=0V to V_{CC} + 1V			10	µA
I_{LO}	Output Leakage Current	$V_{I/O}$=0V to V_{CC}			10	µA
I_{SB1}	V_{CC} Standby Current CMOS	$\overline{CE}$=V_{CC}-.3V to V_{CC} + 1V	Com., Ind.		200	µA
			Mil.		300	µA
I_{SB2}	V_{CC} Standby Current TTL	$\overline{CE}$=2.0V to V_{CC} + 1V			3	mA
I_{CC}	V_{CC} Active Current	f=5MHz; I_{OUT}=0mA			80	mA
V_{IL}	Input Low Voltage				0.8	V
V_{IH}	Input High Voltage			2.0		V
V_{OL}	Output Low Voltage	I_{OL}=2.1mA			.45	V
V_{OH}	Output High Voltage	I_{OH}=-400µA		2.4		V

A.C. Read Characteristics

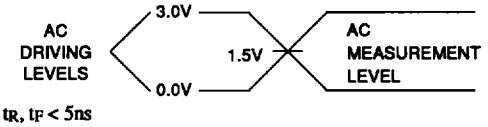
Symbol	Parameter	AT28C256-15		AT28C256-20		AT28C256-25		AT28C256-35		Units
		Min	Max	Min	Max	Min	Max	Min	Max	
t_{ACC}	Address to Output Delay		150		200		250		350	ns
t_{CE} (1)	$\overline{CE}$ to Output Delay		150		200		250		350	ns
t_{OE} (2)	$\overline{OE}$ to Output Delay	0	70	0	80	0	100	0	100	ns
t_{DF} (3,4)	$\overline{CE}$ or $\overline{OE}$ to Output Float	0	50	0	55	0	60	0	70	ns
t_{OH}	Output Hold from $\overline{OE}$, $\overline{CE}$ or Address, whichever occurred first	0		0		0		0		ns

A.C. Read Waveforms



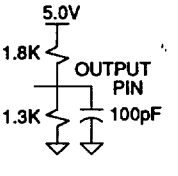
Notes:
1. $\overline{CE}$ may be delayed up to $t_{ACC} - t_{CE}$ after the address transition without impact on t_{ACC}.
2. $\overline{OE}$ may be delayed up to $t_{CE} - t_{OE}$ after the falling edge of $\overline{CE}$ without impact on t_{CE} or by $t_{ACC} - t_{OE}$ after an address change without impact on t_{ACC}.
3. t_{DF} is specified from $\overline{OE}$ or $\overline{CE}$ whichever occurs first ($C_L = 5pF$).
4. This parameter is characterized and is not 100% tested.

Input Test Waveforms and Measurement Level



t_R, $t_F < 5ns$

Output Test Load



Pin Capacitance (f=1MHz T=25°C) (4)

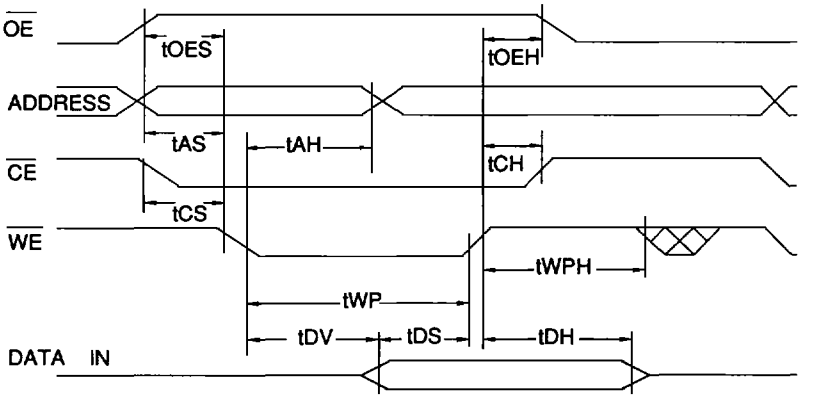
	Typ	Max	Units	Conditions
C_{IN}	4	6	pF	$V_{IN} = 0V$
C_{OUT}	8	12	pF	$V_{OUT} = 0V$

A.C. Write Characteristics

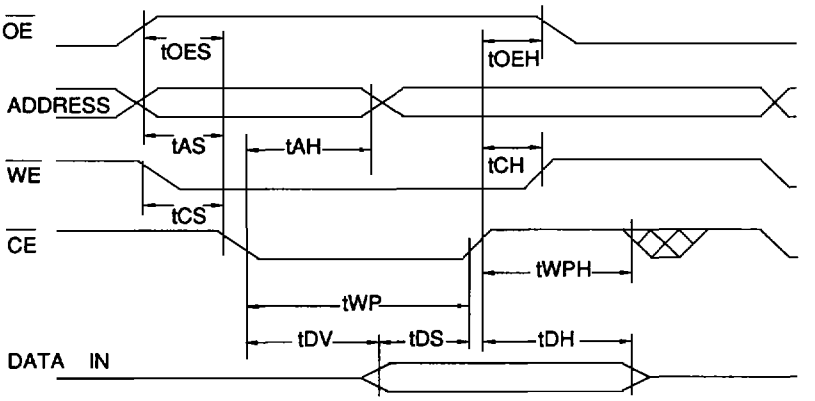
Symbol	Parameter		Min	Max	Units
t_{AS}, t_{OES}	Address, $\overline{OE}$ Set-up Time		0		ns
t_{AH}	Address Hold Time		50		ns
t_{CS}	Chip Select Set-up Time		0		ns
t_{CH}	Chip Select Hold Time		0		ns
t_{WP}	Write Pulse Width ($\overline{WE}$ or $\overline{CE}$)		100		ns
t_{DS}	Data Set-up Time		50		ns
t_{DH},t_{OEH}	Data, $\overline{OE}$ Hold Time		0		ns
t_{DV}	Time to Data Valid		NR(1)		
t_{WC}	Write Cycle Time	AT28C256		10	ms
		AT28C256F		3.0	ms

Note: 1. NR = No Restiction

A.C. Write Waveforms- $\overline{WE}$ Controlled



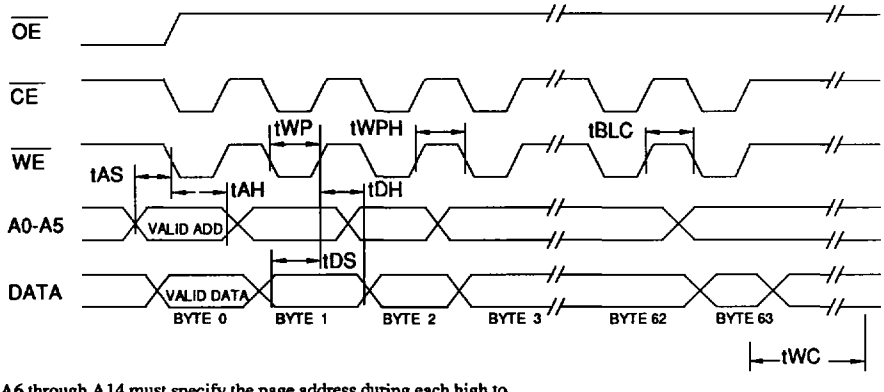
A.C. Write Waveforms- $\overline{CE}$ Controlled



Page Mode Characteristics

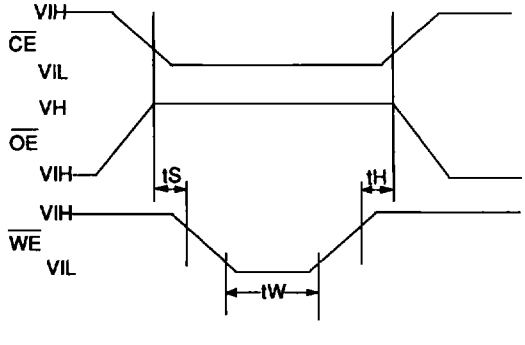
Symbol	Parameter		Min	Max	Units
t_{WC}	Write Cycle Time	AT28C256		10	ms
		AT28C256F		3.0	ms
t_{AS}	Address Set-up Time		0		ns
t_{AH}	Address Hold Time		50		ns
t_{DS}	Data Set-up Time		50		ns
t_{DH}	Data Hold Time		0		ns
t_{WP}	Write Pulse Width		100		ns
t_{BLC}	Byte Load Cycle Time			150	µs
t_{WPH}	Write Pulse Width High		50		ns

Page Mode Write Waveforms



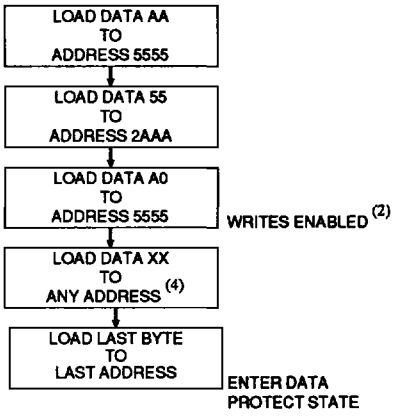
Notes: A6 through A14 must specify the page address during each high to low transition of $\overline{WE}$ (or $\overline{CE}$).
$\overline{OE}$ must be high only when $\overline{WE}$ and $\overline{CE}$ are both low.

Chip Erase Waveforms

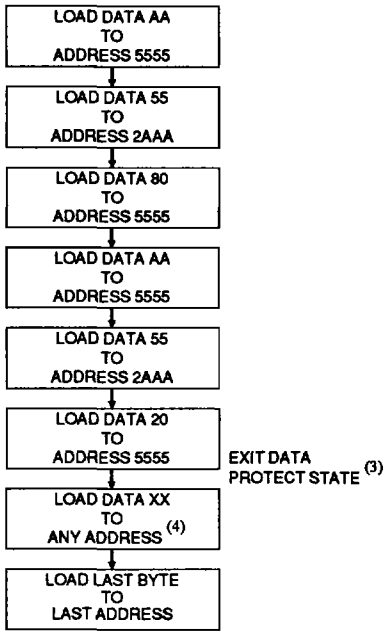


$t_S = t_H = 5\mu sec$ (min.)
t_W = 10msec (min.)
$V_H = 12.0V \pm 0.5V$

Software Data Protection Enable Algorithm [1]

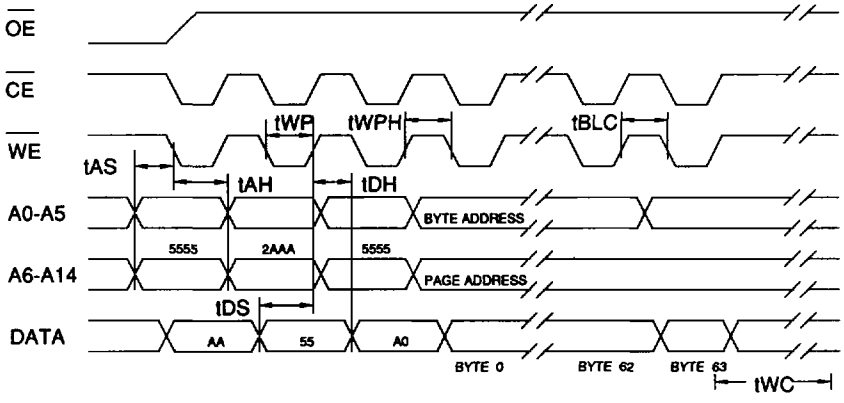


Software Data Protection Disable Algorithm [1]



Notes for software program code:
1. Data Format: I/O7 - I/O0 (Hex);
   Address Format: A14 - A0 (Hex).
2. Write Protect state will be activated at end of write even if no other data is loaded.
3. Write Protect state will be deactivated at end of write period even if no other data is loaded.
4. 1 to 64 bytes of data are loaded.

Software Protected Write Cycle Waveforms



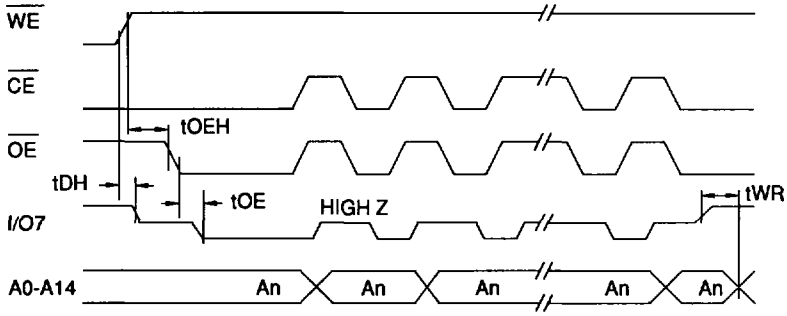
Notes: A6 through A14 must specify the page address during each high to low transition of $\overline{WE}$ (or $\overline{CE}$) after the software code has been entered.
$\overline{OE}$ must be high only when $\overline{WE}$ and $\overline{CE}$ are both low.

$\overline{\text{Data}}$ Polling Characteristics[1]

Symbol	Parameter	Min	Typ	Max	Units
t_{DH}	Data Hold Time	0			ns
t_{OEH}	$\overline{OE}$ Hold Time	0			ns
t_{OE}	$\overline{OE}$ to Output Delay			100	ns
t_{WR}	Write Recovery Time	0			ns

Note: 1. These parameters are characterized and not 100% tested.

$\overline{\text{Data}}$ Polling Waveforms

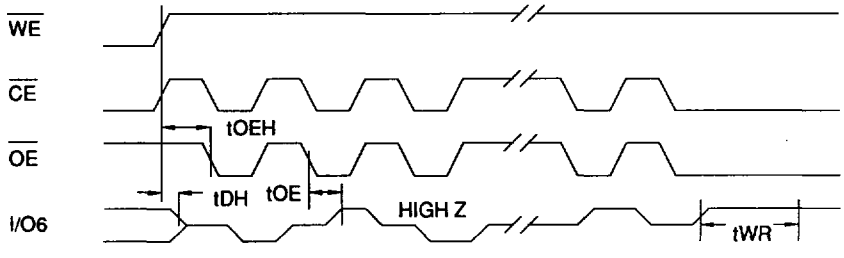


Toggle Bit Characteristics[1]

Symbol	Parameter	Min	Typ	Max	Units
t_{DH}	Data Hold Time	10			ns
t_{OEH}	$\overline{OE}$ Hold Time	10			ns
t_{OE}	$\overline{OE}$ to Output Delay			100	ns
t_{OEHP}	$\overline{OE}$ High Pulse	150			ns
t_{WR}	Write Recovery Time	0			ns

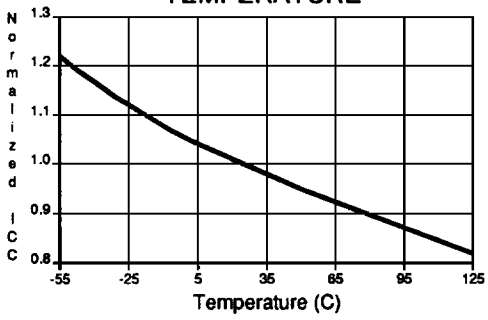
Note: 1. These parameters are characterized and not 100% tested.

Toggle Bit Waveforms

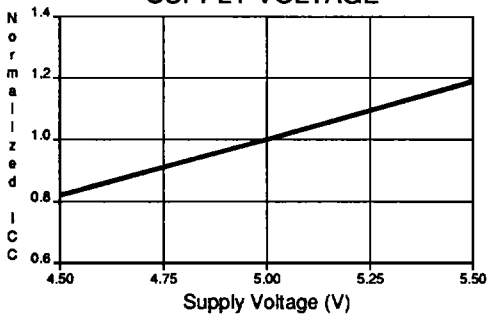


Notes:
1. Toggling either $\overline{OE}$ or $\overline{CE}$ or both $\overline{OE}$ and $\overline{CE}$ will operate toggle bit.
2. Beginning and ending state of I/O6 will vary.
3. Any address location may be used but the address should not vary.

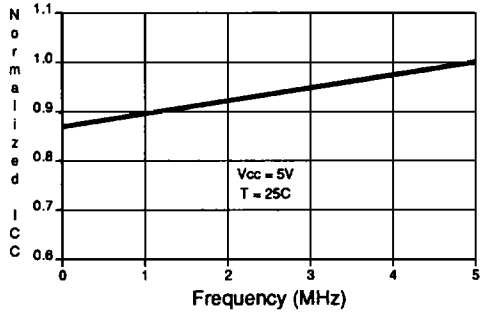
NORMALIZED SUPPLY CURRENT vs. TEMPERATURE



NORMALIZED SUPPLY CURRENT vs. SUPPLY VOLTAGE



NORMALIZED SUPPLY CURRENT vs. ADDRESS FREQUENCY



Ordering Information

tACC (ns)	ICC (mA)		Ordering Code	Package	Operation Range
	Active	Standby			
150	80	0.2	AT28C256(E,F)-15DC AT28C256(E,F)-15FC AT28C256(E,F)-15JC AT28C256(E,F)-15LC AT28C256(E,F)-15PC AT28C256(E,F)-15UC	28D6 28F 32J 32L 28P6 28U	Commercial (0°C to 70°C)
			AT28C256(E,F)-15DI AT28C256(E,F)-15FI AT28C256(E,F)-15JI AT28C256(E,F)-15LI AT28C256(E,F)-15PI AT28C256(E,F)-15UI	28D6 28F 32J 32L 28P6 28U	Industrial (-40°C to 85°C)
150	80	0.3	AT28C256(E,F)-15DM AT28C256(E,F)-15FM AT28C256(E,F)-15LM AT28C256(E,F)-15UM	28D6 28F 32L 28U	Military (-55°C to 125°C)
			AT28C256(E,F)-15DM/883 AT28C256(E,F)-15FM/883 AT28C256(E,F)-15LM/883 AT28C256(E,F)-15UM/883	28D6 28F 32L 28U	Military/883C Class B, Fully Compliant (-55°C to 125°C)
200	80	0.2	AT28C256(E,F)-20DC AT28C256(E,F)-20FC AT28C256(E,F)-20JC AT28C256(E,F)-20LC AT28C256(E,F)-20PC AT28C256(E,F)-20UC	28D6 28F 32J 32L 28P6 28U	Commercial (0°C to 70°C)
			AT28C256(E,F)-20DI AT28C256(E,F)-20FI AT28C256(E,F)-20JI AT28C256(E,F)-20LI AT28C256(E,F)-20PI AT28C256(E,F)-20UI	28D6 28F 32J 32L 28P6 28U	Industrial (-40°C to 85°C)
200	80	0.3	AT28C256(E,F)-20DM AT28C256(E,F)-20FM AT28C256(E,F)-20LM AT28C256(E,F)-20UM	28D6 28F 32L 28U	Military (-55°C to 125°C)
			AT28C256(E,F)-20DM/883 AT28C256(E,F)-20FM/883 AT28C256(E,F)-20LM/883 AT28C256(E,F)-20UM/883	28D6 28F 32L 28U	Military/883C Class B, Fully Compliant (-55°C to 125°C)
250	80	0.2	AT28C256(E,F)-25DC AT28C256(E,F)-25FC AT28C256(E,F)-25JC AT28C256(E,F)-25LC AT28C256(E,F)-25PC AT28C256(E,F)-25UC AT28C256-W	28D6 28F 32J 32L 28P6 28U DIE	Commercial (0°C to 70°C)

Ordering Information

t_{ACC} (ns)	I_{CC} (mA)		Ordering Code	Package	Operation Range
	Active	Standby			
250	80	0.2	AT28C256(E,F)-25DI AT28C256(E,F)-25FI AT28C256(E,F)-25JI AT28C256(E,F)-25LI AT28C256(E,F)-25PI AT28C256(E,F)-25UI	28D6 28F 32J 32L 28P6 28U	Industrial (-40°C to 85°C)
250	80	0.3	AT28C256(E,F)-25DM AT28C256(E,F)-25FM AT28C256(E,F)-25LM AT28C256(E,F)-25UM	28D6 28F 32L 28U	Military (-55°C to 125°C)
			AT28C256(E,F)-25DM/883 AT28C256(E,F)-25FM/883 AT28C256(E,F)-25LM/883 AT28C256(E,F)-25UM/883	28D6 28F 32L 28U	Military/883C Class B, Fully Compliant (-55°C to 125°C)
300	80	0.3	AT28C256(E,F)-30DM/883 AT28C256(E,F)-30FM/883 AT28C256(E,F)-30LM/883 AT28C256(E,F)-30UM/883	28D6 28F 32L 28U	Military/883C Class B, Fully Compliant (-55°C to 125°C)
350	80	0.3	AT28C256(E,F)-35DM/883 AT28C256(E,F)-35FM/883 AT28C256(E,F)-35LM/883 AT28C256(E,F)-35UM/883	28D6 28F 32L 28U	Military/883C Class B, Fully Compliant (-55°C to 125°C)
150	80	0.35	5962-88525 07 UX 5962-88525 07 XX 5962-88525 07 YX 5962-88525 07 ZX	28U 28D6 32L 28F	Military/883C Class B, Fully Compliant (-55°C to 125°C)
			5962-88525 06 UX 5962-88525 06 XX 5962-88525 06 YX 5962-88525 06 ZX	28U 28D6 32L 28F	Military/883C Class B, Fully Compliant (-55°C to 125°C)
200	80	0.35	5962-88525 04 UX 5962-88525 04 XX 5962-88525 04 YX 5962-88525 04 ZX	28U 28D6 32L 28F	Military/883C Class B, Fully Compliant (-55°C to 125°C)
250	80	0.35	5962-88525 03 UX 5962-88525 03 XX 5962-88525 03 YX 5962-88525 03 ZX	28U 28D6 32L 28F	Military/883C Class B, Fully Compliant (-55°C to 125°C)
			5962-88525 05 UX 5962-88525 05 XX 5962-88525 05 YX 5962-88525 05 ZX	28U 28D6 32L 28F	Military/883C Class B, Fully Compliant (-55°C to 125°C)
300	80	0.35	5962-88525 02 UX 5962-88525 02 XX 5962-88525 02 YX 5962-88525 02 ZX	28U 28D6 32L 28F	Military/883C Class B, Fully Compliant (-55°C to 125°C)

Ordering Information

t_{ACC} (ns)	I_{CC} (mA)		Ordering Code	Package	Operation Range
	Active	Standby			
350	80	0.35	5962-88525 01 UX 5962-88525 01 XX 5962-88525 01 YX 5962-88525 01 ZX	28U 28D6 32L 28F	Military/883C Class B, Fully Compliant (-55°C to 125°C)

Package Type	
28D6	28 Lead, 0.600" Wide, Non-Windowed, Ceramic Dual Inline Package (Cerdip)
28F	28 Lead, Non-Windowed, Ceramic Bottom-Brazed Flat Package (Flatpack)
32J	32 Lead, Plastic J-Leaded Chip Carrier (PLCC)
32L	32 Pad, Non-Windowed, Ceramic Leadless Chip Carrier (LCC)
28P6	28 Lead, 0.600" Wide, Plastic Dual Inline Package (PDIP)
28U	28 Pin, Ceramic Pin Grid Array (PGA)
W	Die
Options	
Blank	Standard Device: Endurance = 10K Write Cycles; Write Time = 10 ms
E	High Endurance Option: Endurance = 100K Write Cycles
F	Fast Write Option: Write Time = 3 ms